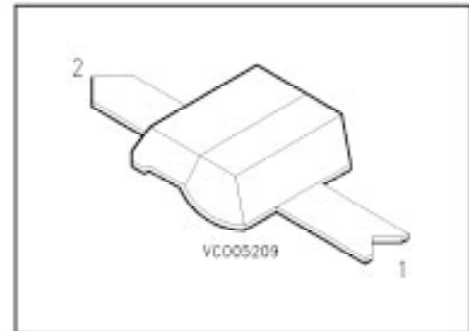


SIEMENS

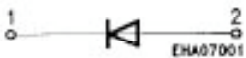
Silicon Schottky Diode

BAT 30

- RF detector
- Low-power mixer
- Zero bias
- Very low capacitance
- For frequencies up to 25 GHz



ESD: Electrostatic discharge sensitive device, observe handling precautions!

Type	Frequency band (GHz)	Ordering Code	Pin Configuration	Package ¹⁾
BAT 30	... 25 (I, K)	Q62702-A764	Pointed anode 	S1

Maximum Ratings

Parameter	Symbol	Values	Unit
Reverse voltage	V_R	6.5	V
Forward current	I_F	50	mA
Junction temperature	T_j	150	°C
Storage temperature range	T_{stg}	- 55 ... + 150	
Operating temperature range	T_{op}	- 55 ... + 150	

¹⁾ For detailed information see chapter Package Outlines.

Electrical Characteristics

at $T_A = 25\text{ }^\circ\text{C}$, unless otherwise specified.

Parameter	Symbol	Values			Unit
		min.	typ.	max.	
Breakdown voltage $I_R = 1\text{ mA}$	$V_{(BR)}$	6.5	–	–	V
Forward voltage $I_F = 1\text{ mA}$ $I_F = 10\text{ mA}$	V_F	– –	0.2 0.6	– –	
Diode capacitance $V_R = 0.15\text{ V}, f = 1\text{ MHz}$	C_T	–	0.14	0.18	pF
Differential resistance $V_F = 0, f = 10\text{ kHz}$	R_D	–	15	–	k Ω

Forward current $I_F = f(V_F)$

